

# 2N5758-2N5760 – NPN 2N6226-2N6228 – PNP

High-reliability discrete products and engineering services since 1977

## COMPLEMENTARY SILICON POWER TRANSISTORS

#### FEATURES:

- Available as "HR" (high reliability) screened per MIL-PRF-19500, JANTX level. Add "HR" suffix to base part number
- Available Non-RoHS (standard) or RoHS compliant (add PBF suffix)

#### MAXIMUM RATINGS

Ratings	Symbol	2N5758 2N6226	2N5759 2N6227	2N5760 2N6228	Unit
Collector-Base Voltage	V <sub>CBO</sub>	100	120	140	V
Collector-Emitter Voltage	V <sub>CEO</sub>	100	120	140	V
Emitter-Base Voltage	V <sub>EBO</sub>	7		V	
Collector Current -Continuous Peak	lc	6 10		А	
Base Current	Iв	4.0		А	
Total Power Dissipation	PD	150		W	
Operating and Storage Temperature Range	TJ, TSTG	-65 to +200		°C	
Thermal Resistance Junction to case	Rejc	1.17		°C/W	

#### ELECTRICAL CHARACTERISTICS @ 25°C unless otherwise noted

Characteristics	Symbol	Min	Max	Unit	
Collector Base Cutoff Current		Ісво			mA
$V_{CB}$ = Rated $V_{CB}$ ,		1680	-	1.0	
Collector Emitter Cutoff Current					
$V_{CE}$ = Rated $V_{CB}$ , $V_{EB(off)}$ = 1.5V		ICEV	-	1.0	mA
$V_{CE}$ = Rated $V_{CB}$ , $V_{EB(off)}$ = 1.5V, $T_C$ = 150°C			-	5.0	
Collector Emitter Cutoff Current					mA
$V_{CE} = \frac{1}{2}$ Rated $V_{CEO}$		I <sub>CEO</sub>	-	1.0	ma
Emitter Base Cutoff Current					
V <sub>BE</sub> = 7V		I <sub>EBO</sub>	-	1.0	mA
Collector Base Breakdown Voltage	2N5758, 2N6226		100	-	
Ic = 200mA	2N5759, 2N6227	BV <sub>CEO</sub>	120	-	V
	2N5760, 2N6228		140	-	
Collector-Emitter Saturation Voltage					
$I_{C} = 3A, I_{B} = 0.3A$		V <sub>CE(sat)</sub>	-	1.0	V
I <sub>C</sub> = 6A, I <sub>B</sub> = 1.2A			-	2.0	
Base-Emitter On-Voltage		N/			V
VCE = 2.0V, I <sub>C</sub> = 3.0A		V <sub>BE(ON)</sub>	-	1.5	v
DC Current Gain	2N5758, 2N6226		25	100	
I <sub>C</sub> = 3A, V <sub>CE</sub> = 2V	2N5759, 2N6227	hfe	20	80	-
	2N5760, 2N6228		15	60	
DC Current Gain	2N5758, 2N6226		5.0	-	
I <sub>C</sub> = 6A, V <sub>CE</sub> = 2V	2N5759, 2N6227	h <sub>FE</sub>	5.0	-	-
	2N5760, 2N6228		5.0	-	
Small Signal Current Gain		Ŀ			
I <sub>C</sub> = 2A, V <sub>CE</sub> = 10V, f = 1KHz		h <sub>fe</sub>	15	-	-



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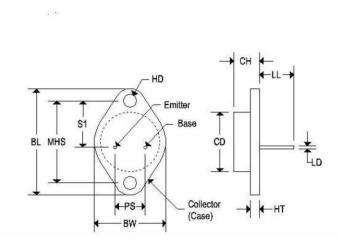
### ELECTRICAL CHARACTERISTICS @ 25°C unless otherwise noted

Characteristics	Symbol	Min	Max	Unit
Current Gain – Bandwidth Product <sup>(2)</sup> I <sub>C</sub> = 0.5A, V <sub>CE</sub> = 20V, f <sub>test</sub> = 0.5MHz	f <sub>T</sub>	1	-	MHz
Output Capacitance $V_{CB} = 10V$ , $I_E = 0$ , $f = 100$ kHz	Cob	-	300	pF

Note 1: Pulse width =  $350\mu s$ , duty cycle  $\leq 0.0$ Note 2:  $f_T = |h_{fe}| \circ f_{test}$ 

### **MECHANICAL CHARACTERISTICS**

Case	ТО-3
Marking	Alpha-numeric
Pin out	See below



	TO-3			
	Inches		Millin	neters
	Min	Max	Min	Max
CD	-	0.875	-	22.220
CH	0.250	0.380	6.860	9.650
HT	0.060	0.135	1.520	3.430
BW	-	1.050	×.	26.670
HD	0.131	0.188	3.330	4.780
LD	0.038	0.043	0.970	1.090
LL	0.312	0.500	7.920	12.700
BL	1.550 REF		39.370 REF	
MHS	1.177	1.197	29.900	30.400
PS	0.420	0.440	10.670	11.180
S1	0.655	0.675	16.640	17.150